IN THE SPECIFICATION

Please replace the paragraph beginning at page 3, line 15 to page 4, line 1, with the following rewritten paragraph:

The non-volatile semiconductor memory device in accordance with one aspect of the invention includes a memory cell array having a plurality of non-volatile memory cells, a decode circuit configured to decode address data as input thereto to select a memory cell from the memory cell array, and a data sense circuit configured to detect and amplify the data of the selected memory cell of the memory cell array. The memory cell array includes an initial setup data region with initial setup data and status data being programmed thereinto. The initial setup data is used for determination of memory operating conditions, and the status data indicates whether the initial setup region is presently normal or not in functionality.

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